

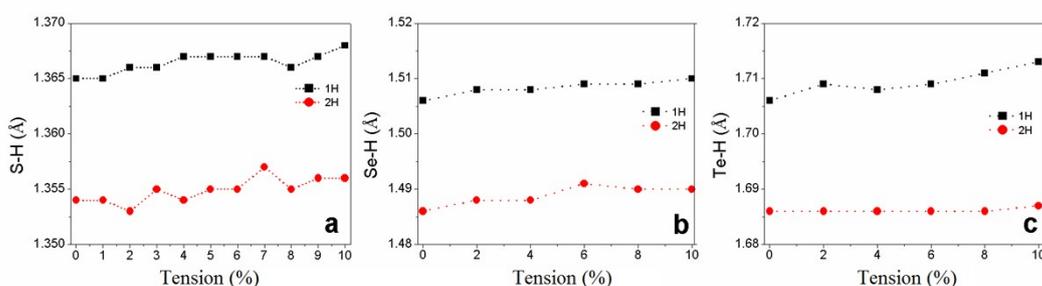
Electronic Properties of Tin Dichalcogenide Monolayers and Effects of Hydrogenation and Tension

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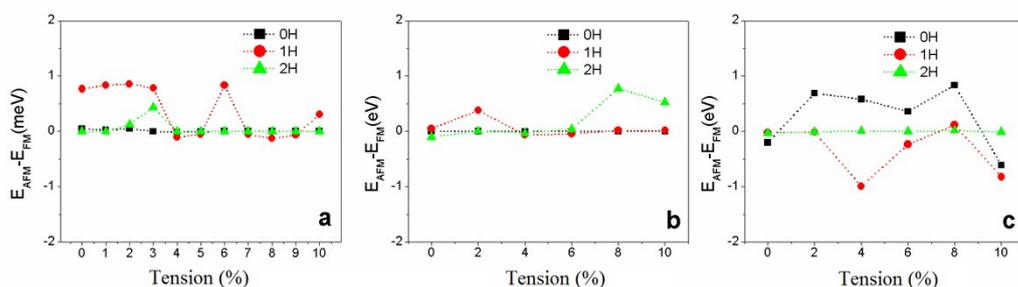
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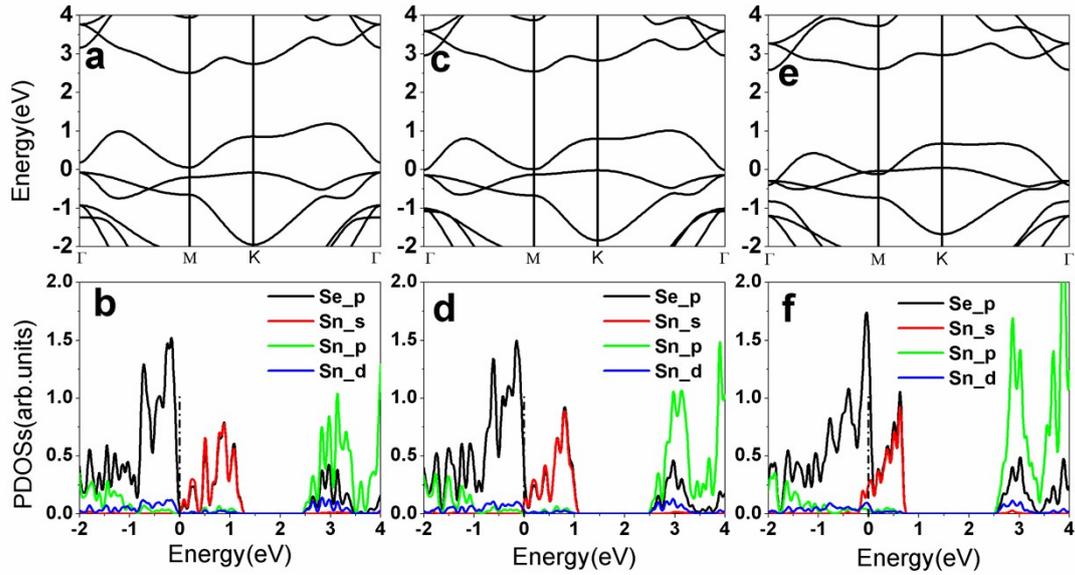
Supporting Data



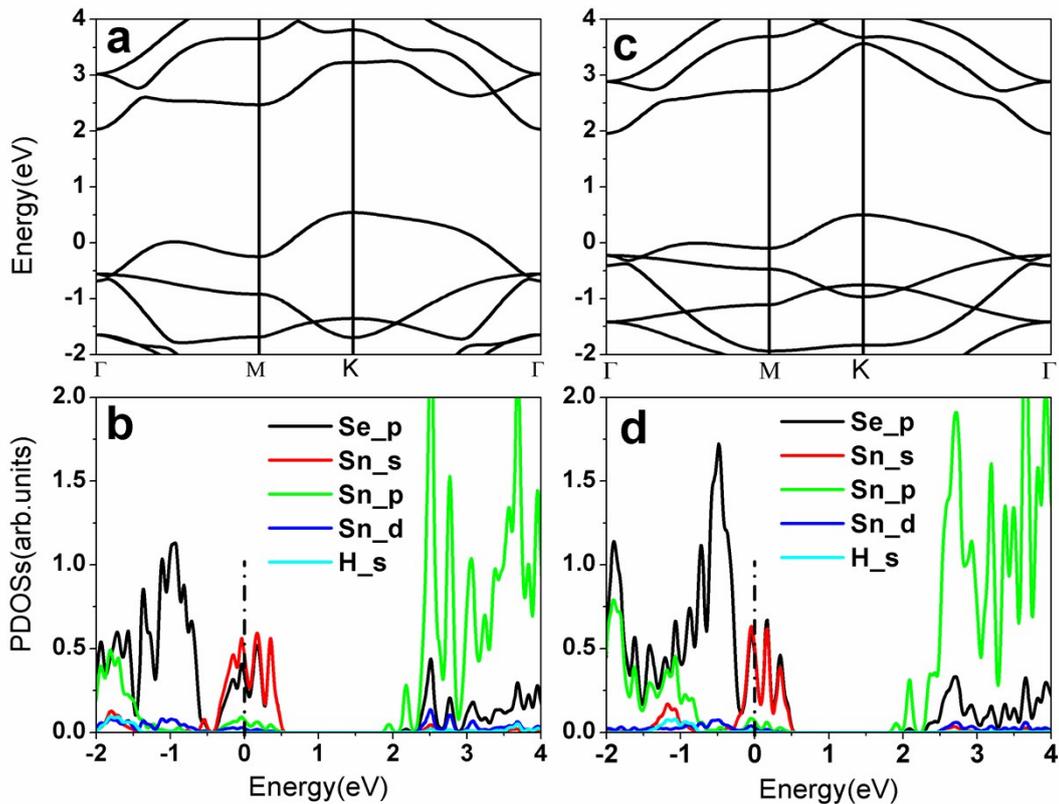
S-1, The bond length of (a) S-H, (b) Se-H, and (c) Te-H on $\text{SnX}_2\text{-nH}$ monolayers ($X = \text{S}, \text{Se}, \text{and Te}; n = 1 \text{ and } 2$).



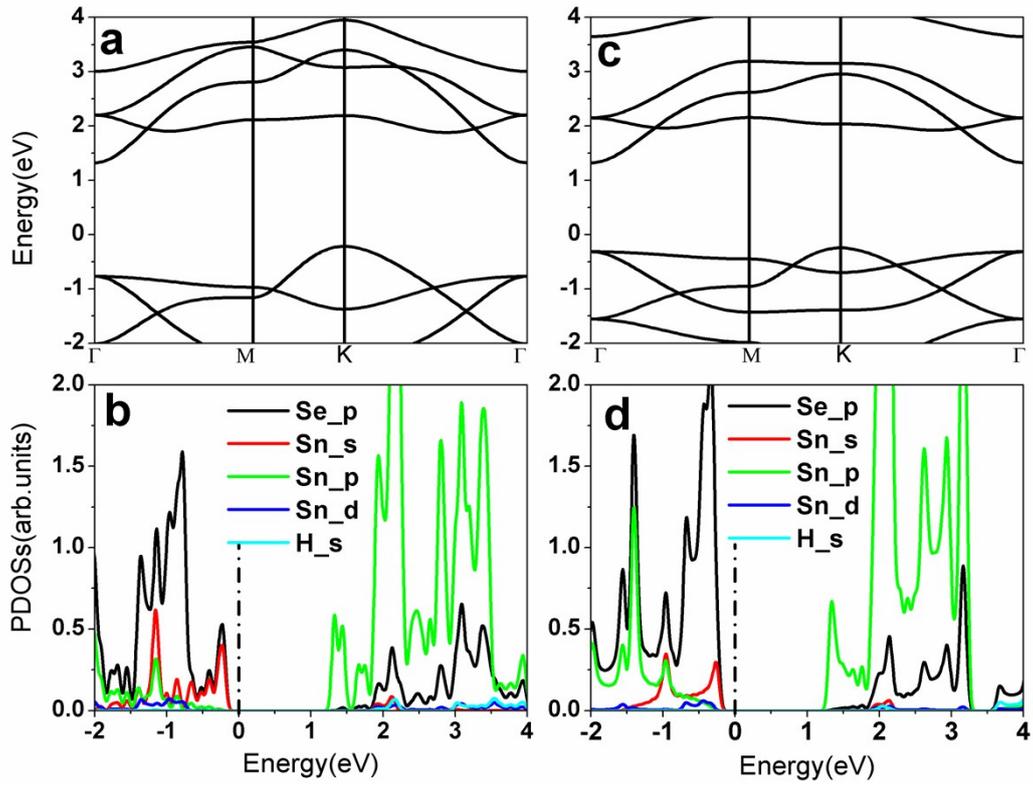
S-2, Total energy difference between ferromagnetic (FM) and anti-ferromagnetic (AFM) states for (a) SnS_2 , (b) SnSe_2 , and (c) SnTe_2 monolayers with and without hydrogenation under tension.



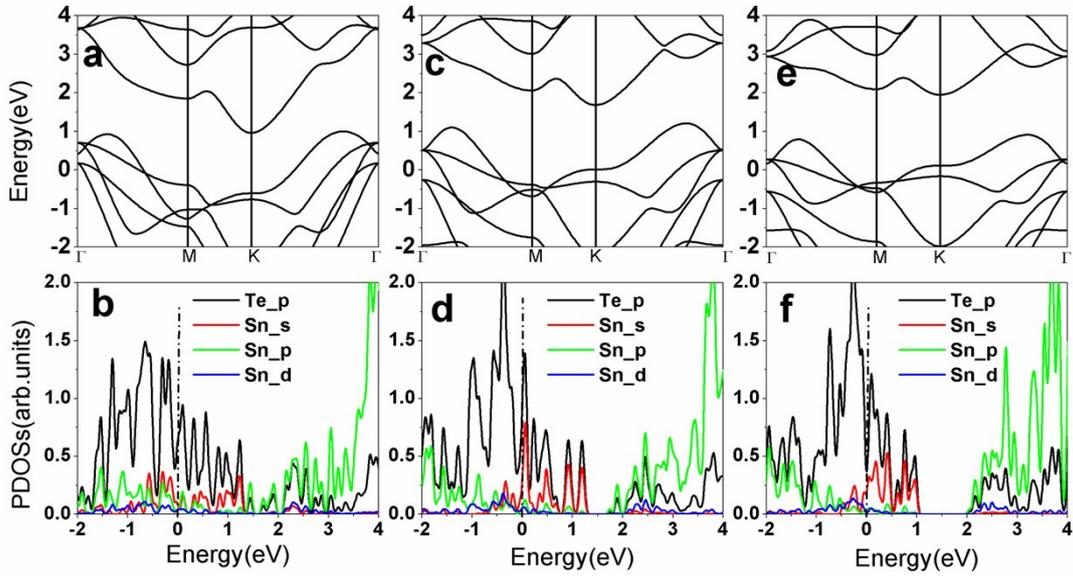
S-3, Calculated band structures of SnSe₂-0H-ML at a tension of (a) 4 %, (c) 6 % and (e) 10% and partial density of states at a tension of (b) 4%, (d) 6 % and (f) 10 %. Fermi level is at 0 eV.



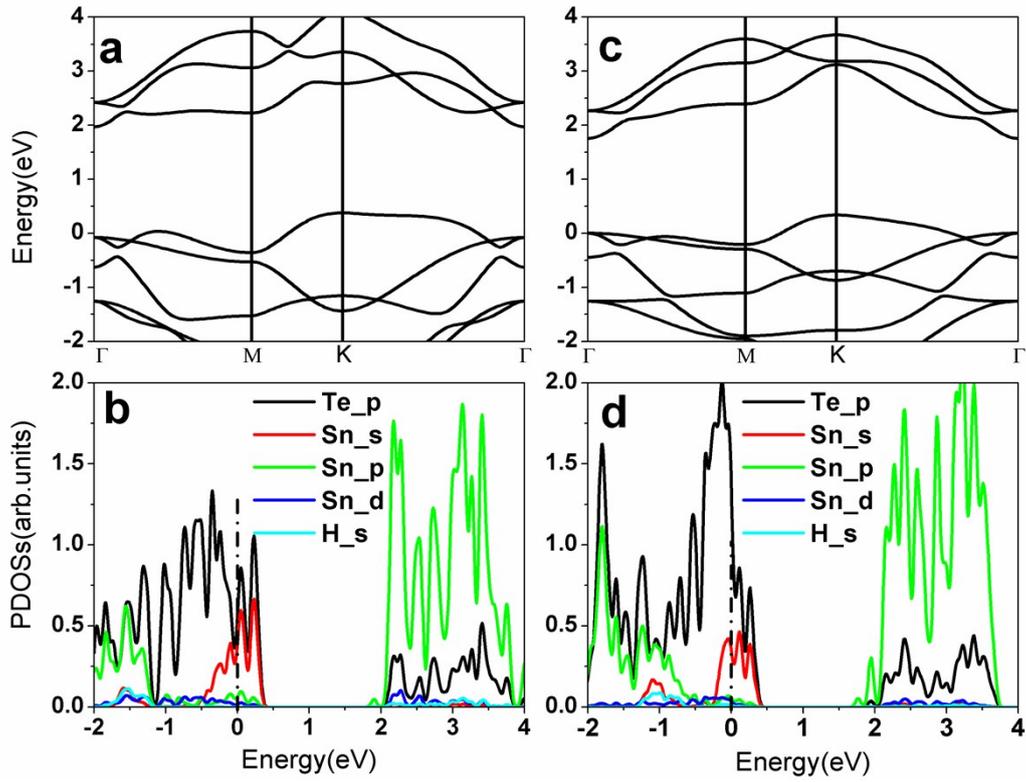
S-4, Calculated band structures of SnSe₂-1H-ML at a tension of (a) 2 % and (c) 10 % and partial density of states at a tension of (b) 2 % and (d) 10 %. Fermi level is at 0 eV.



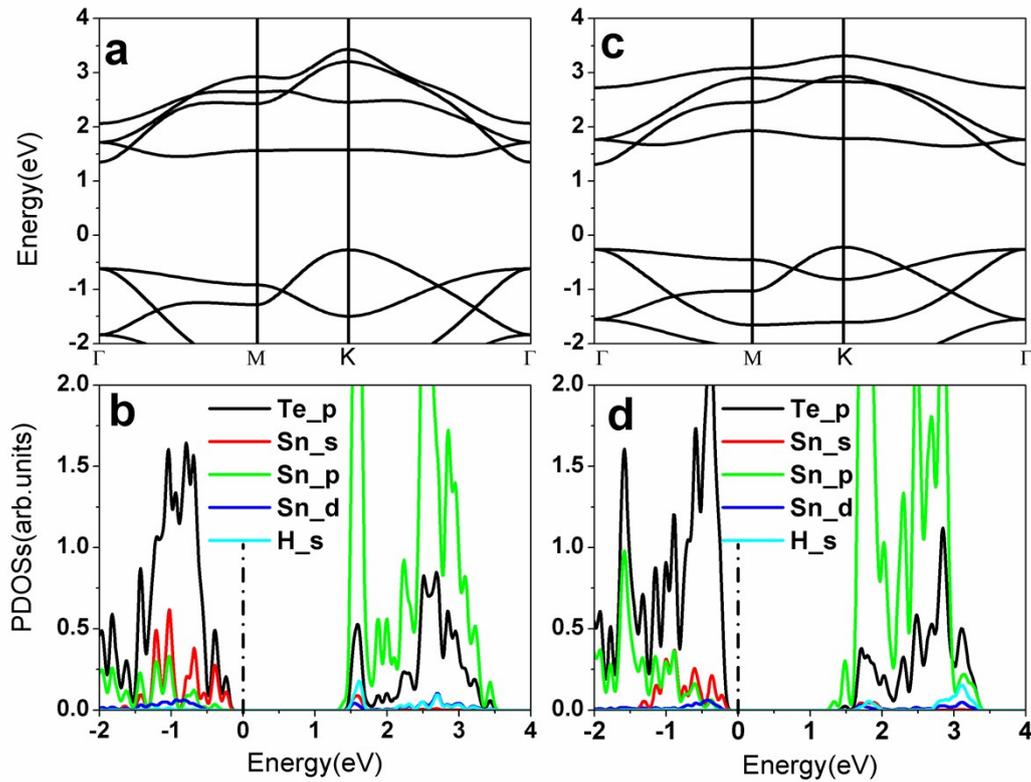
S-5, Calculated band structures of SnSe₂-2H-ML at a tension of (a) 2 % and (c) 10 % and partial density of states at a tension of (b) 2 % and (d) 10 %. Fermi level is at 0 eV.



S-6, Calculated band structures of SnTe₂-0H-ML at a tension of (a) 2 %, (c) 6 % and (e) 10 %, and partial density of states at a tension of (b) 2 %, (d) 6 % and (f) 10 %. Fermi level is at 0 eV.



S-7, Calculated band structures of SnTe₂-1H-ML at a tension of (a) 2 % and (c) 10 % and partial density of states at a tension of (b) 2 % and (d) 10 %. Fermi level is at 0 eV.



S-8, Calculated bond structures of SnTe₂-2H-ML at a tension of (a) 2 % and (c) 10 % and partial density of states at a tension of (b) 2 % and (d) 10 %. Fermi level is at 0 eV.